



2SA2153

Bipolar Transistor -50V, -2A, Low VCE(sat), PNP Single PCP

ON Semiconductor®

<http://onsemi.com>

Applications

- Voltage regulators, relay drivers, lamp drivers, electrical equipment

Features

- Adoption of MBIT process
- Low saturation voltage
- Large current capacity and wide ASO

Specifications

Absolute Maximum Ratings at Ta=25°C

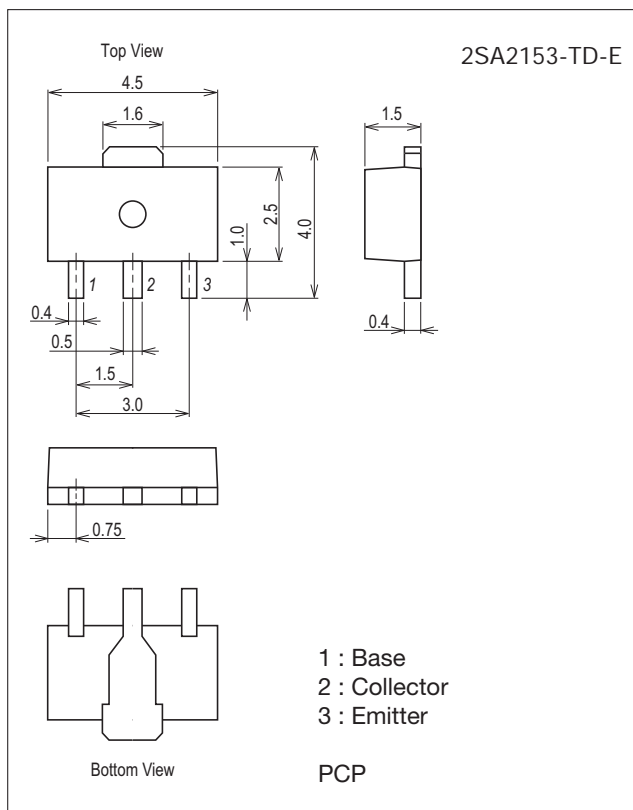
Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V _{CB0}		-50	V
Collector-to-Emitter Voltage	V _{CE0}		-50	V
Emitter-to-Base Voltage	V _{EB0}		-6	V
Collector Current	I _C		-2	A
Collector Current (Pulse)	I _{CP}		-4	A
Base Current	I _B		-400	mA

Continued on next page.

Package Dimensions

unit : mm (typ)

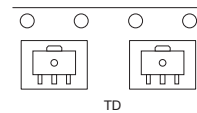
7007B-004



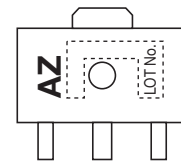
Product & Package Information

- Package : PCP
- JEITA, JEDEC : SC-62, SOT-89, TO-243
- Minimum Packing Quantity : 1,000 pcs./reel

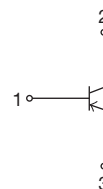
Packing Type: TD



Marking



Electrical Connection



2SA2153

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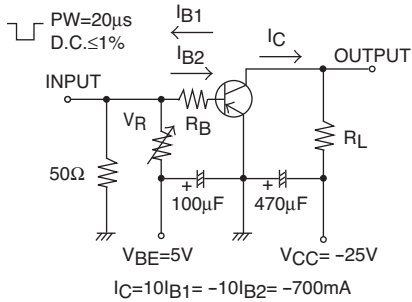
Parameter	Symbol	Conditions	Ratings	Unit
Collector Dissipation	PC	When mounted on ceramic substrate (450mm ² ×0.8mm)	1.3	W
		T _c =25°C	3.5	W
Junction Temperature	T _j		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Electrical Characteristics at T_a=25°C

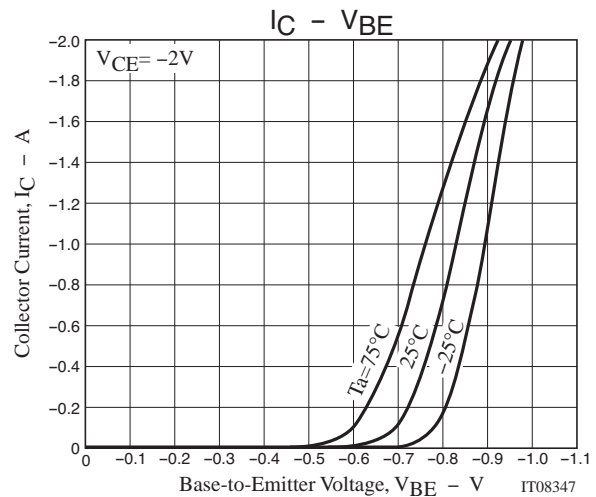
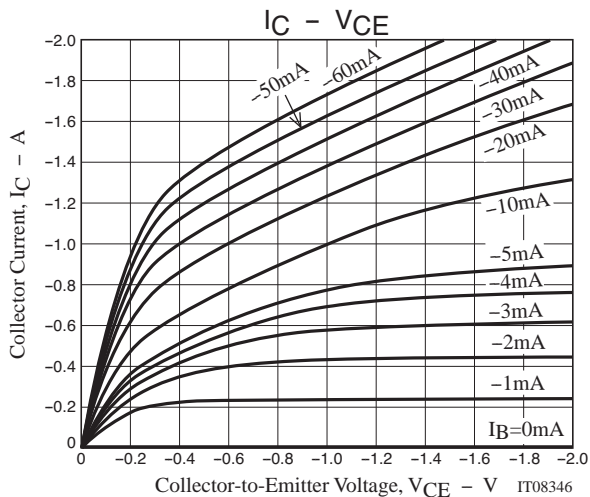
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I _{CBO}	V _{CB} =-40V, I _E =0A			-1	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} =-4V, I _C =0A			-1	μA
DC Current Gain	h _{FE1}	V _{CE} =-2V, I _C =-100mA	200		560	
	h _{FE2}	V _{CE} =-2V, I _C =-1.5A	40			
Gain-Bandwidth Product	f _T	V _{CE} =-10V, I _C =-300mA		420		MHz
Output Capacitance	C _{ob}	V _{CB} =-10V, f=1MHz		16		pF
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	I _C =-1A, I _B =-50mA	-0.2		-0.4	V
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =-1A, I _B =-50mA	-0.9		-1.2	V
Collector-to-Base Breakdown Voltage	V _{(BR)CBO}	I _C =-10μA, I _E =0A	-50			V
Collector-to-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C =-1mA, R _{BE} =∞	-50			V
Emitter-to-Base Breakdown Voltage	V _{(BR)EBO}	I _E =-10μA, I _C =0A	-6			V
Turn-ON Time	t _{on}			35		ns
Storage Time	t _{stg}	See specified Test Circuit.		200		ns
Fall Time	t _f			24		ns

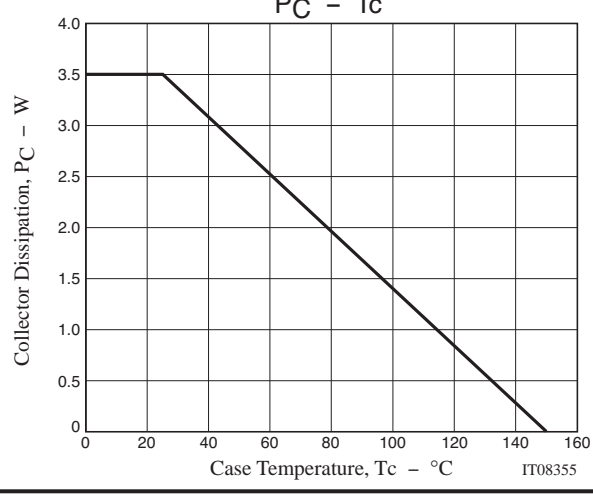
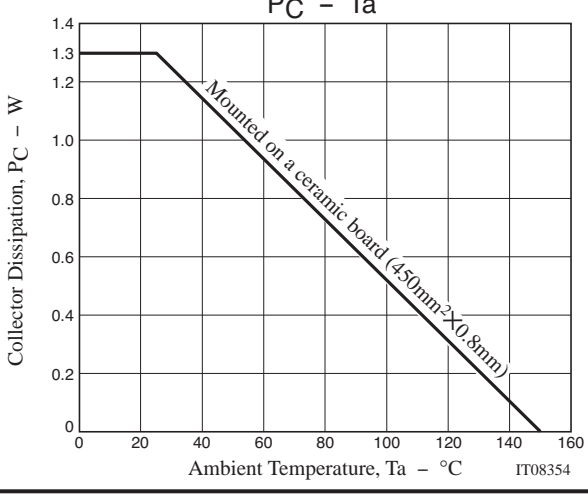
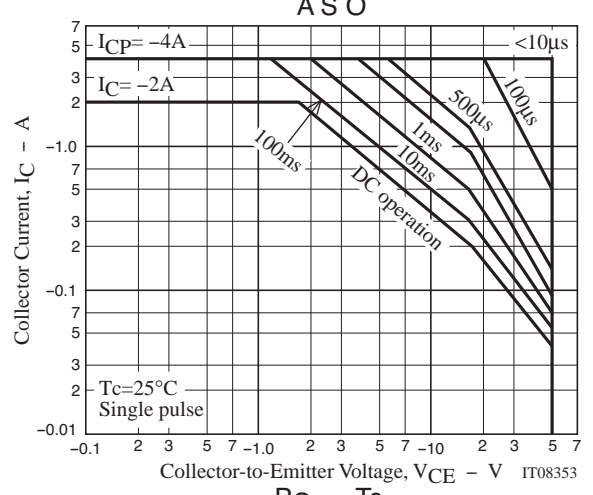
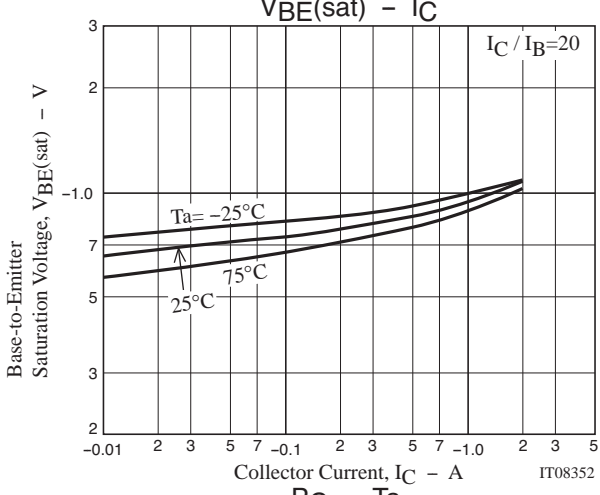
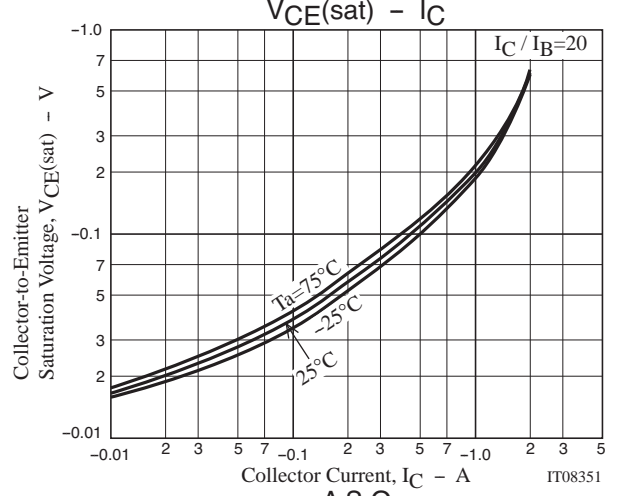
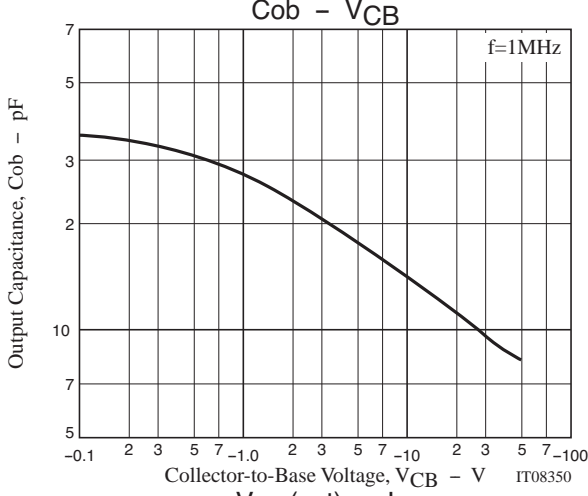
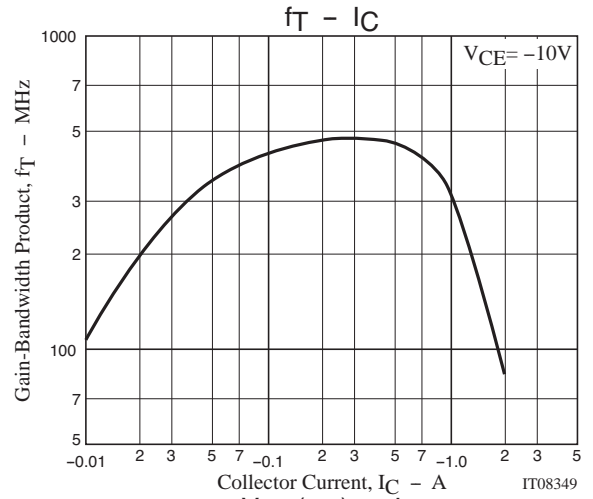
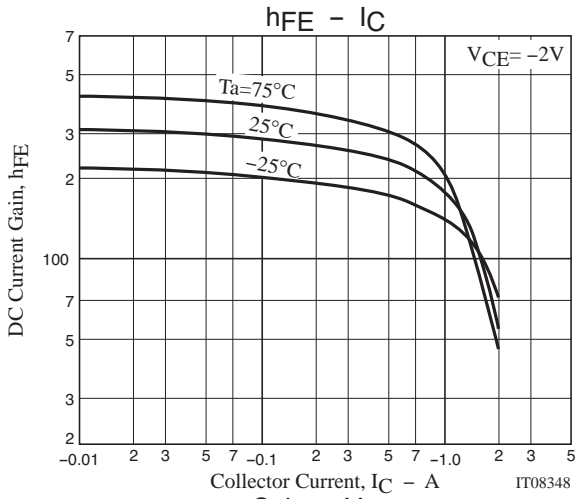
Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo
2SA2153-TD-E	PCP	1,000pcs./reel	Pb Free





Embossed Taping Specification

2SA2153-TD-E

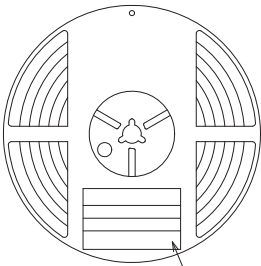
1. Packing Format

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
PCP	PCP	1,000	4,000	24,000	4 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

Reel label, Inner box label
(unit : mm)

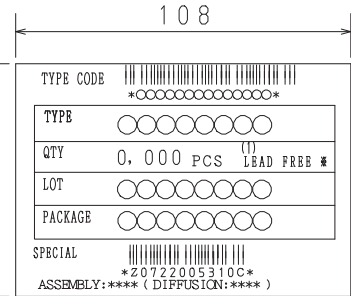
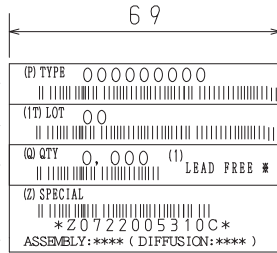
Outer box label
It is a label at the time of factory shipments.
The form of a label may change in physical distribution process.

Packing method



Reel label

Type No.
LOT No.
Quantity
Origin



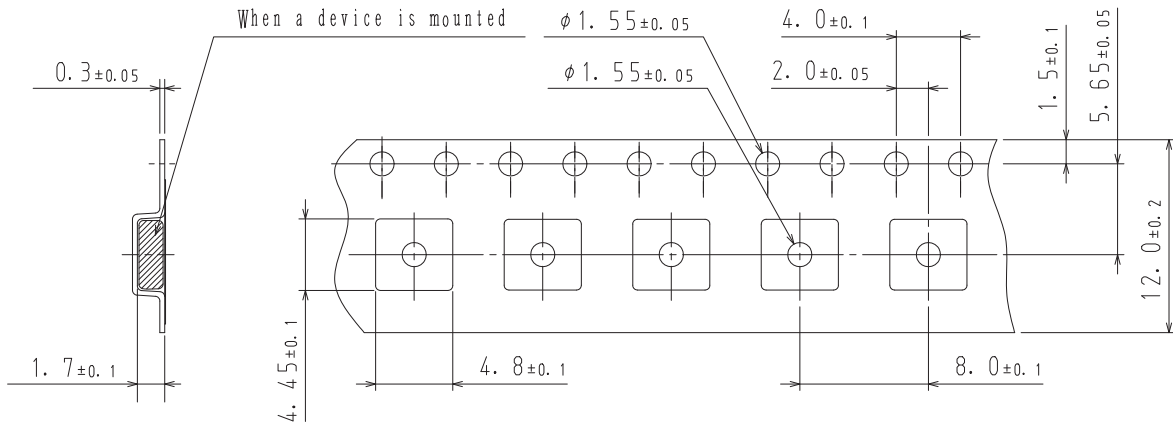
NOTE (1)

The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

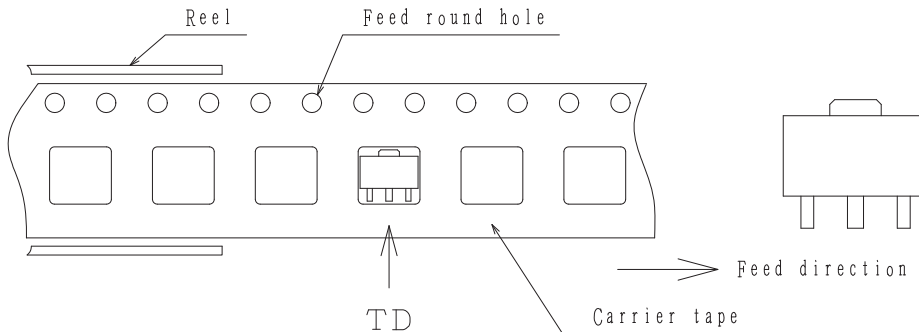
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



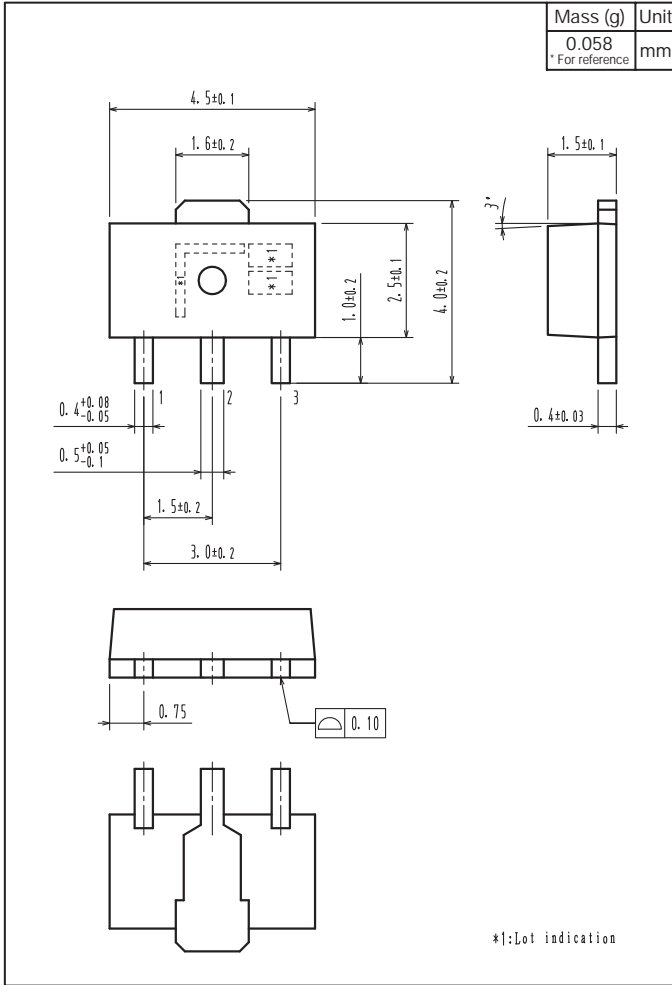
2-2. Device placement direction



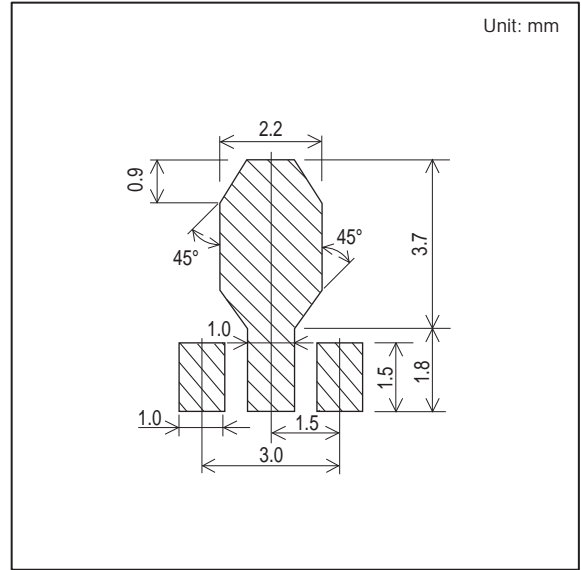
Those with pin 1 index on the feed hole side.....TD

Outline Drawing

2SA2153-TD-E



Land Pattern Example



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